

# 1SS81

Silicon Epitaxial Planar Diode for High Voltage Switching

# HITACHI

ADE-208-148A (Z)

Rev. 1

Jul. 1995

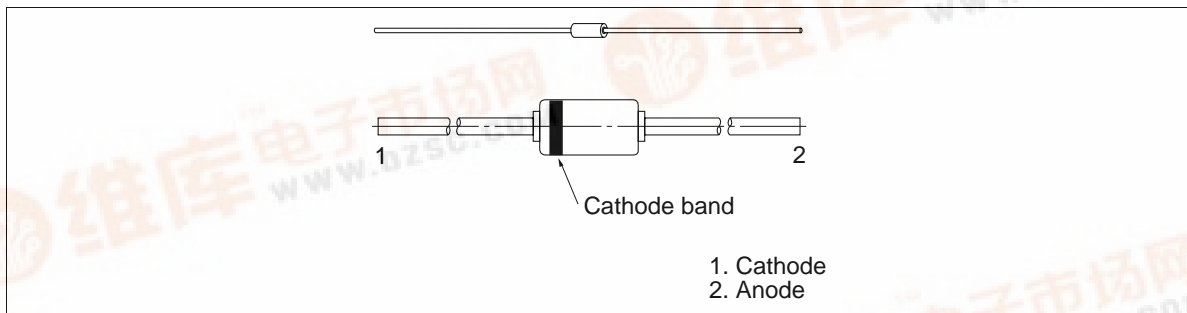
## Features

- High reverse voltage. ( $V_R = 150V$ )
- High reliability with glass seal.

## Ordering Information

Type No.	Cathode band	Package Code
1SS81	Verdure	DO-35

## Outline



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## 1SS81

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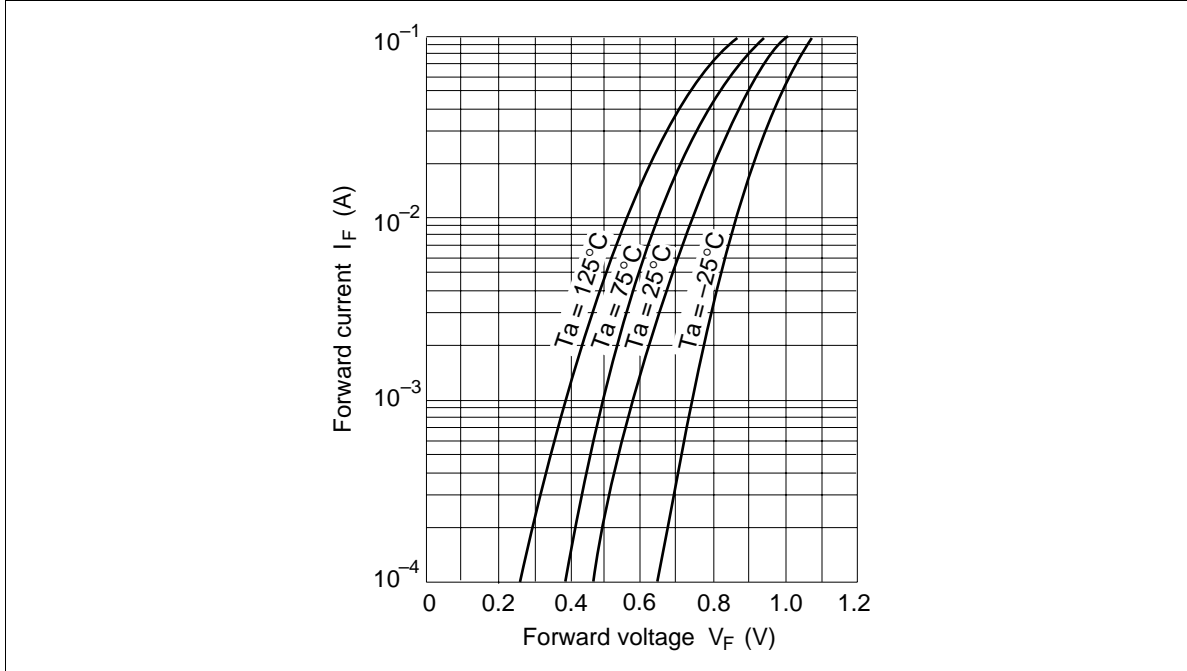
### Absolute Maximum Ratings\*2 (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}^{*1}$	200	V
Reverse voltage	$V_R$	150	V
Peak forward current	$I_{FM}$	625	mA
Non-Repetitive peak forward surge current	$I_{FSM}^{*2}$	1	A
Average forward current	$I_O$	200	mA
Power dissipation	$P_d$	400	mW
Junction temperature	$T_j$	175	°C
Storage temperature	$T_{stg}$	-65 to +175	°C

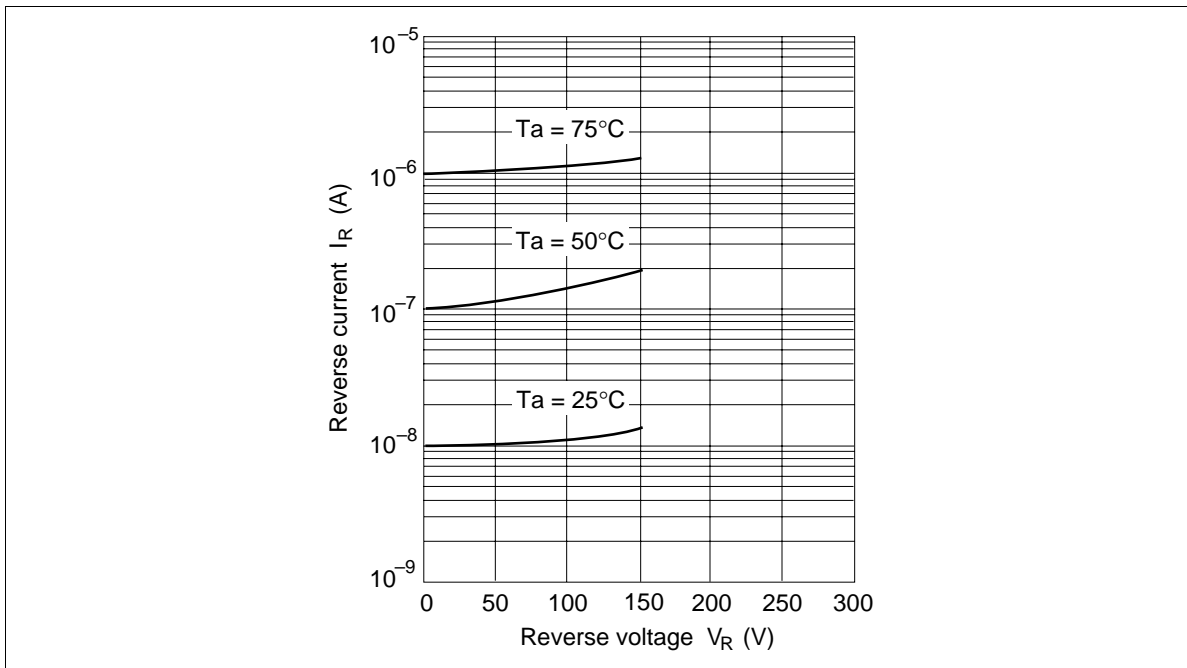
Notes: 1. Reverse voltage in excess of peak reverse voltage may deteriorate electrical characteristic.  
2. Within 1s forward surge current.

### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_F$	—	—	1.0	V	$I_F = 100\text{mA}$
Reverse current	$I_{R1}$	—	—	0.2	$\mu\text{A}$	$V_R = 150\text{V}$
	$I_{R2}$	—	—	100		$V_R = 200\text{V}$
Capacitance	$C$	—	1.5	—	pF	$V_R = 0\text{V}, f = 1\text{MHz}$
Reverse recovery time	$t_{rr}$	—	—	100	ns	$I_F = I_R = 30\text{mA}, I_{rr} = 3\text{mA}, R_L = 100\Omega$



**Fig.1 Forward current Vs. Forward voltage**



**Fig.2 Reverse current Vs. Reverse voltage**

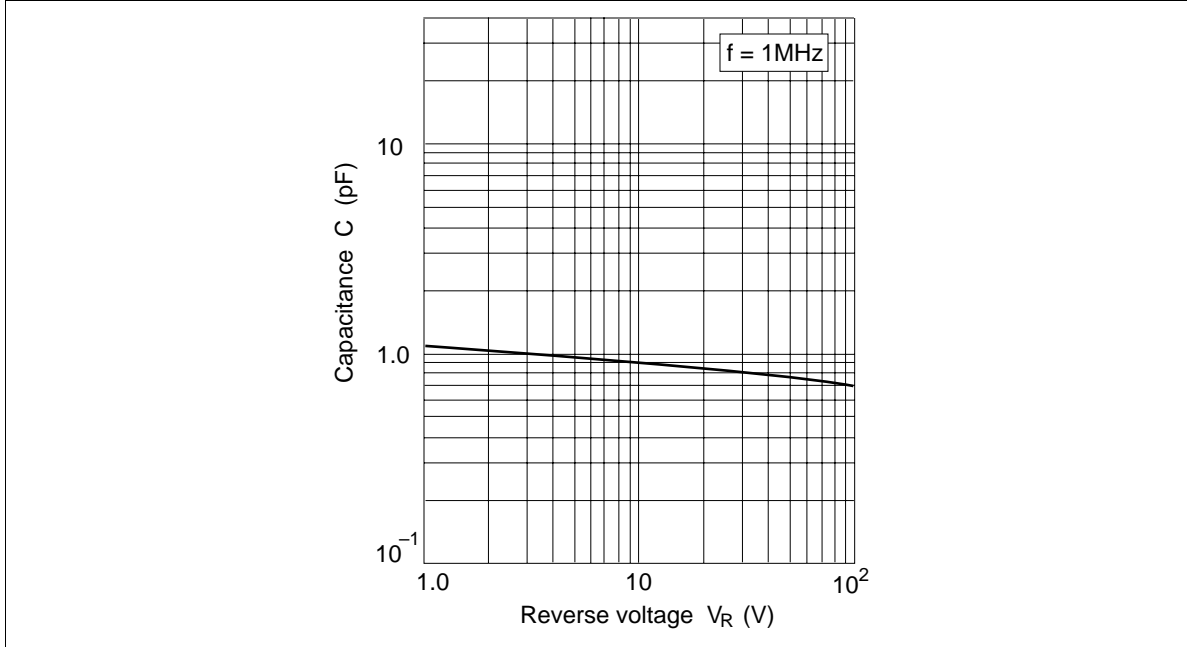
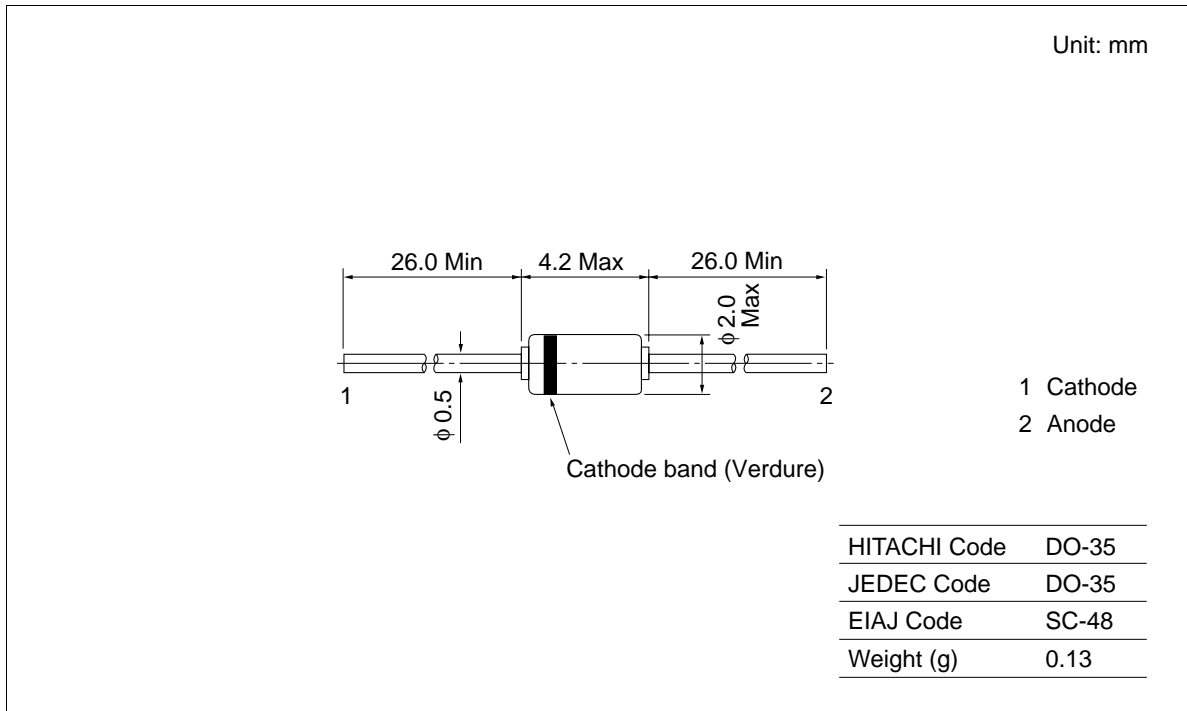


Fig.3 Capacitance Vs. Reverse voltage

**Package Dimensions**

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